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Team Nexperia

# PDTD123E series

NPN 500 mA, 50 V resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$ 

Rev. 02 — 16 November 2009

Product data sheet

## 1. Product profile

### 1.1 General description

500 mA NPN Resistor-Equipped Transistors (RET) family.

Table 1. Product overview

Type number	Package			PNP complement		
	NXP	JEITA	JEDEC			
PDTD123EK	SOT346	SC-59A	TO-236	PDTB123EK		
PDTD123ES[1]	SOT54	SC-43A	TO-92	PDTB123ES		
PDTD123ET	SOT23	-	TO-236AB	PDTB123ET		

<sup>[1]</sup> Also available in SOT54A and SOT54 variant packages (see Section 2).

### 1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- 500 mA output current capability
- Reduces component count
- Reduces pick and place costs
- ±10 % resistor ratio tolerance

### 1.3 Applications

- Digital application in automotive and industrial segments
- Controlling IC inputs

- Cost saving alternative for BC817 series in digital applications
- Switching loads

### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	50	V
I <sub>O</sub>	output current (DC)		-	-	500	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		0.9	1.0	1.1	



## 2. Pinning information

Table 3. **Pinning** Simplified outline Pin **Description Symbol** SOT54 1 input (base) 2 output (collector) 3 GND (emitter) 001aab347 SOT54A 1 input (base) 2 output (collector) 3 GND (emitter) 001aab348 006aaa145 **SOT54** variant 1 input (base) 2 output (collector) 3 GND (emitter) 001aab447 006aaa145 **SOT23, SOT346** 1 input (base) 3 2 GND (emitter) 3 output (collector) 2

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006aaa144

## 3. Ordering information

Table 4. Ordering information

Type number	Package						
	Name	Description	Version				
PDTD123EK	SC-59A	plastic surface mounted package; 3 leads	SOT346				
PDTD123ES[1]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54				
PDTD123ET	-	plastic surface mounted package; 3 leads	SOT23				

<sup>[1]</sup> Also available in SOT54A and SOT54 variant packages (see Section 2 and Section 9).

## 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PDTD123EK	E3
PDTD123ES	D123ES
PDTD123ET	*7T

<sup>[1] \* = -:</sup> made in Hong Kong

## 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	50	V
$V_{EBO}$	emitter-base voltage	open collector	-	10	V
VI	input voltage				
	positive		-	+12	V
	negative		-	-10	V
I <sub>O</sub>	output current (DC)		-	500	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	[1]		
	SOT346		-	250	mW
	SOT54		-	500	mW
	SOT23		-	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		<del>-</del> 65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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<sup>\* =</sup> p: made in Hong Kong

<sup>\* =</sup> t: made in Malaysia

<sup>\* =</sup> W: made in China

## 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	SOT346		-	-	500	K/W
	SOT54		-	-	250	K/W
	SOT23		-	-	500	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

## 7. Characteristics

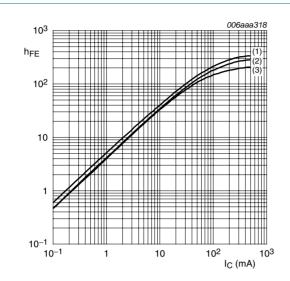
Table 8. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = 40 \text{ V}; I_{E} = 0 \text{ A}$	-	-	100	nA
	current	$V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}$	-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = 50 \text{ V}; I_{B} = 0 \text{ A}$	-	-	0.5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	2	mA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 50 \text{ mA}$	40	-	-	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 2.5 \text{ mA}$	-	-	0.3	V
$V_{\text{I(off)}}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	0.6	1.1	1.8	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 20 \text{ mA}$	1.0	1.5	2.0	V
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		0.9	1.0	1.1	
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V; } I_E = i_e = 0 \text{ A;}$ f = 100 MHz	-	7	-	pF

006aaa319

NPN 500 mA resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$ 



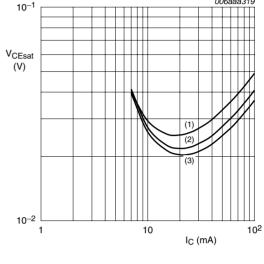
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 1. DC current gain as a function of collector current; typical values



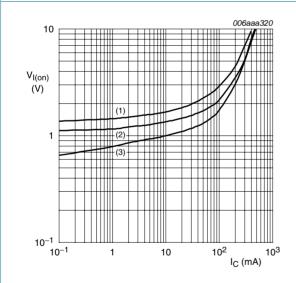
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values



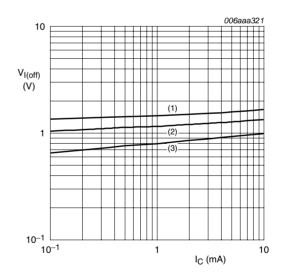
$$V_{CE} = 0.3 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 3. On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

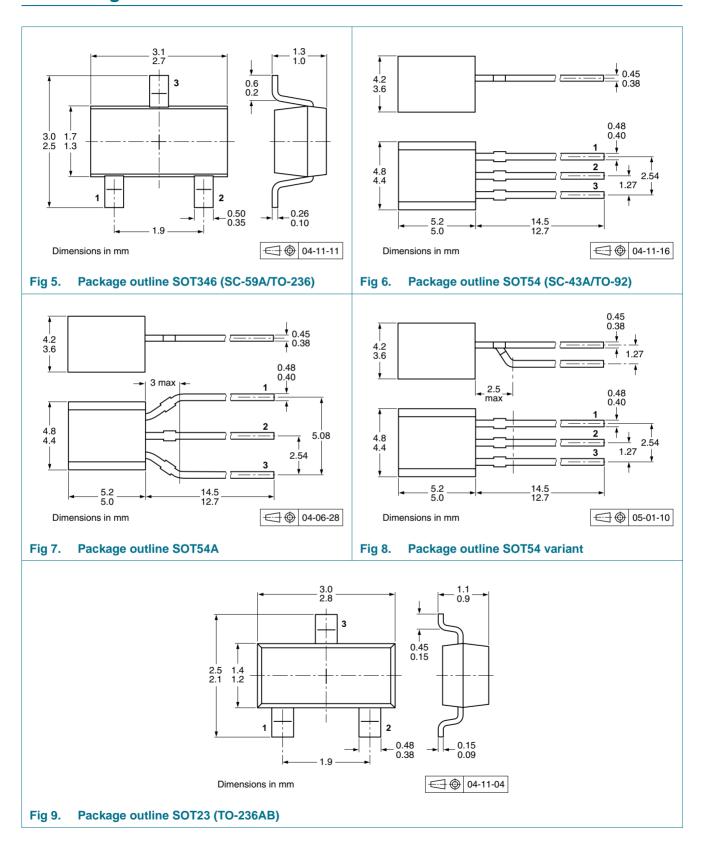
(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 4. Off-state input voltage as a function of collector current; typical values

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## 8. Package outline



**Product data sheet** 

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NPN 500 mA resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$ 

## **Packing information**

Table 9. **Packing methods** 

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity			
			3000	5000	10000	
PDTD123EK	SOT346	4 mm pitch, 8 mm tape and reel	-115	-	-135	
PDTD123ES	SOT54	bulk, straight leads	-	-412	-	
	SOT54A	tape and reel, wide pitch	-	-	-116	
		tape ammopack, wide pitch	-	-	-126	
	SOT54 variant	bulk, delta pinning	-	-112	-	
PDTD123ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235	

<sup>[1]</sup> For further information and the availability of packing methods, see Section 12.



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NPN 500 mA resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$ 

## 10. Revision history

### Table 10. Revision history

**Product data sheet** 

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTD123E_SER_2	20091116	Product data sheet	-	PDTD123E_SER_1
Modifications:		eet was changed to reflect w legal definitions and disc		
PDTD123E_SER_1	20050408	Product data sheet	-	-

## 11. Legal information

#### 11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# PDTD123E series

### NPN 500 mA resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

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